

isc Silicon PNP Power Transistors

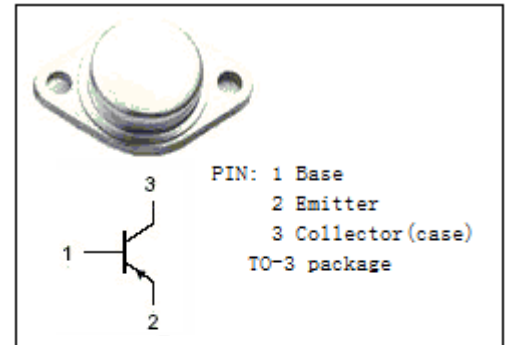
2N6379

DESCRIPTION

- Low Collector Saturation Voltage
- High DC Current Gain
- High Power Dissipation

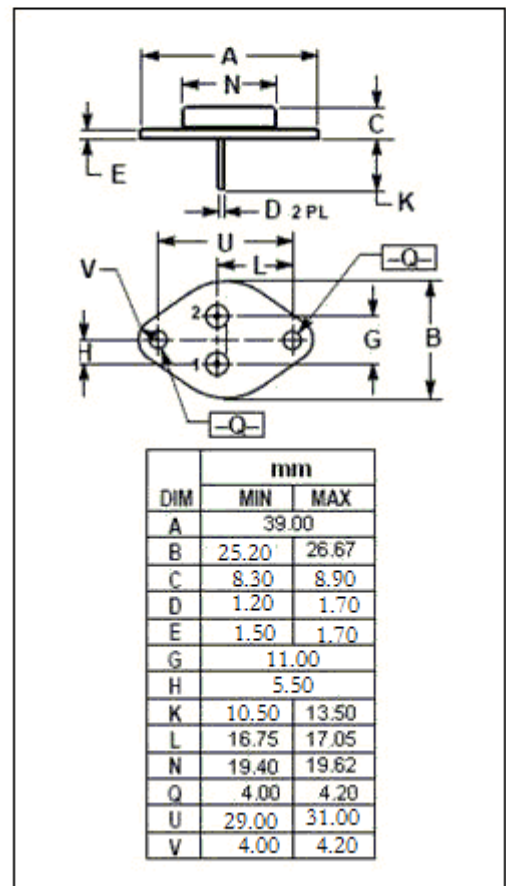
APPLICATIONS

- Designed for use in industrial-military power amplifier and switching circuit application.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|------------------------------|---------|------|
| V _{CBO} | Collector-Base Voltage | -140 | V |
| V _{CE0} | Collector-Emitter Voltage | -120 | V |
| V _{EBO} | Emitter-Base Voltage | -6 | V |
| I _C | Collector Current-Continuous | -50 | A |
| I _B | Base Current-Continuous | -20 | A |
| P _C | Collector Power Dissipation | 250 | W |
| T _J | Junction Temperature | -65~200 | °C |
| T _{stg} | Storage Temperature | -65~200 | °C |



isc Silicon PNP Power Transistors**2N6379****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-------------------------|--------------------------------------|--|-----|------|------|------|
| V _{CE(sat)1} ★ | Collector-Emitter Saturation Voltage | I _C = -20A; I _B = -2A | | | -1.2 | V |
| V _{CE(sat)2} ★ | Collector-Emitter Saturation Voltage | I _C = -50A; I _B = -10A | | | -3.0 | V |
| V _{BE(sat)1} ★ | Base-Emitter Saturation Voltage | I _C = -20A; I _B = -2A | | | -1.8 | V |
| V _{BE(sat)1} ★ | Base-Emitter Saturation Voltage | I _C = -50A; I _B = -10A | | | -3.5 | V |
| I _{EBO} | Collector Cutoff Current | V _{EB} = -6V; I _E = 0 | | | -0.1 | mA |
| h _{FE1} ★ | DC Current Gain | I _C = -1A; V _{CE} = -4V | 50 | | | |
| h _{FE2} ★ | DC Current Gain | I _C = -20A; V _{CE} = -4V | 30 | | 120 | |
| h _{FE3} ★ | DC Current Gain | I _C = -50A; V _{CE} = -4V | 10 | | | |

★:Pulse Test:Pulse Width=300us,Duty Cycle=2.0%